



### **60V N-Channel Enhancement Mode MOSFET**

Voltage

60 V

**Current** 

35 A

#### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@20A<21m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_D@12A<24m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

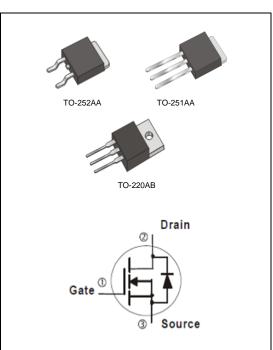
• Case: TO-251AA,TO-252AA,TO-220AB Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• TO-251AA Approx. Weight: 0.0104 ounces, 0.297grams

• TO-252AA Approx. Weight: 0.0105 ounces, 0.297grams

• TO-220AB Approx. Weight: 0.067 ounces, 2 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	TO-251AA	TO-220AB	TO-252AA	UNITS
Drain-Source Voltage		$V_{DS}$	60			V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20			
Continuous Drain Current	T <sub>C</sub> =25°C		35			
	T <sub>C</sub> =100°C	l <sub>D</sub>	22			A
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>				
Power Dissipation	T <sub>C</sub> =25°C	PD	63	104	63	W
	T <sub>C</sub> =100°C		25	42	25	
Continuous Drain Current	T <sub>A</sub> =25°C	1	4.7			А
	T <sub>A</sub> =70°C	l <sub>D</sub>	3.8			
Power Dissipation	T <sub>A</sub> =25°C		1.1	2.0	1.1	W
Power Dissipation	T <sub>A</sub> =70°C	Pb	0.7	1.3	0.7	
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	42			mJ
Operating Junction and		T <sub>J</sub> ,T <sub>STG</sub>		°C		
Storage Temperature Range			-55~150			
Typical Thermal Resistance <sup>(Note 4,5)</sup>						
- Junction to Case		$R_{ hetaJC}$	2	1.2	2	°C/W
- Junction to Ambient		$R_{ hetaJA}$	110	62	110	

Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1	1.73	2.5	
Drain Course On State Besisters	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	17	21	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =12A	-	20	24	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> =30V, I <sub>D</sub> =15A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	28	-	nC
Gate-Source Charge	$Q_gs$		-	3.5	-	
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =10V	-	6.5	-	
Input Capacitance	Ciss		-	1680	-	pF
Output Capacitance	Coss	$V_{DS}$ =20V, $V_{GS}$ =0V, $I_{S}$ =1,0MHZ	-	115	-	
Reverse Transfer Capacitance	Crss	I=1.UIVITZ	-	85	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	7.2	-	
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}=30V, I_{D}=1A,$		38	-	
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}=10V, R_G=6\Omega$ (Note 1,2)	-	34	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	8.2	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	ı		_	-	35	А
Diode Forward Current	I <sub>S</sub>		_			
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.67	1	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 4. The maximum current rating is package limited.
- 5. R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =29A,  $V_{DD}$ =25V,  $V_{GS}$ =10V,  $R_{G}$ =25ohm, Starting  $T_{J}$ =25 $^{\circ}$ C
- 7. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

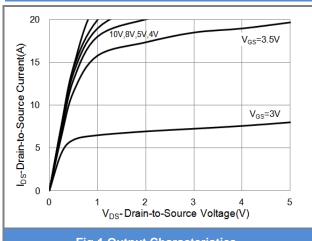


Fig.1 Output Characteristics

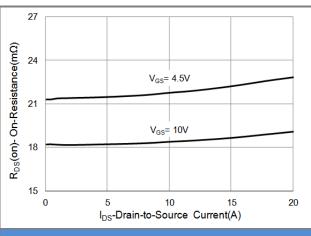


Fig.3 On-Resistance vs. Drain Current

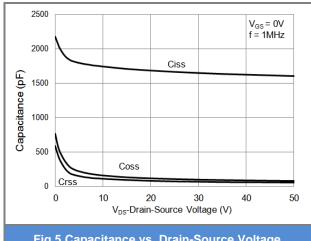


Fig.5 Capacitance vs. Drain-Source Voltage

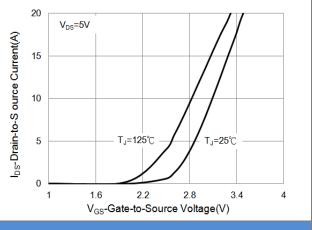


Fig.2 Transfer Characteristics

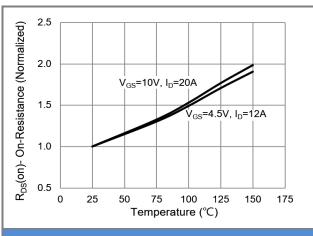


Fig.4 On-Resistance vs. Junction temperature

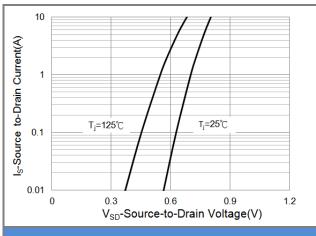


Fig.6 Source-Drain Diode Forward Voltage





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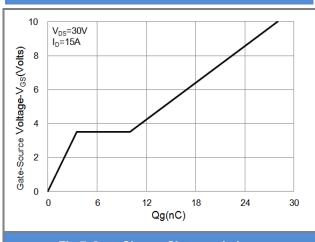


Fig.7 Gate-Charge Characteristics

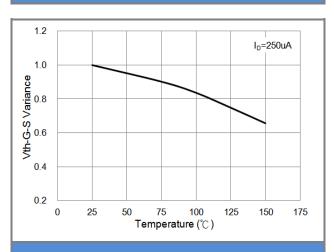


Fig.9 Threshold Voltage Variation with Temperature

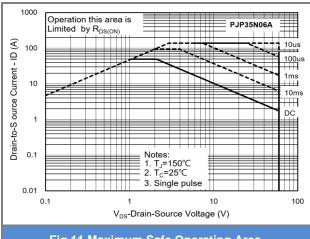


Fig.11 Maximum Safe Operating Area

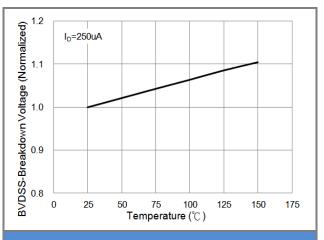


Fig.8 Breakdown Voltage Variation vs. Temperature

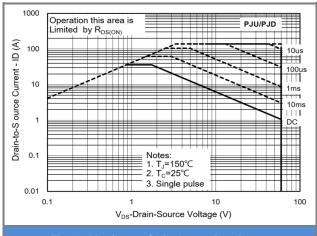


Fig.10 Maximum Safe Operating Area





#### **TYPICAL CHARACTERISTIC CURVES**

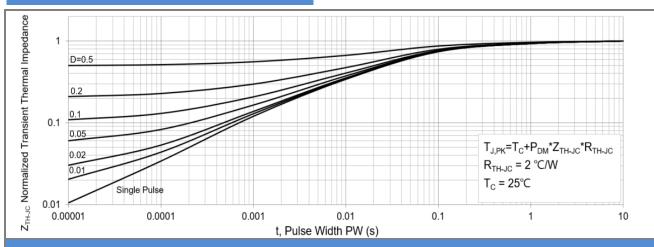


Fig.13 PJU/PJD Normalized Transient Thermal Impedance vs. Pulse Width

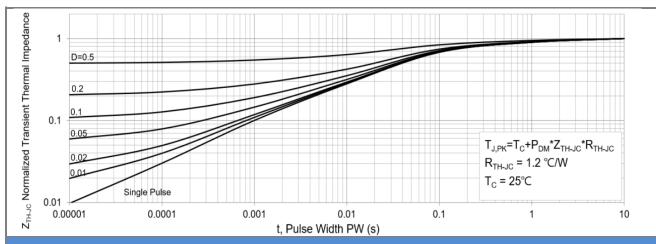
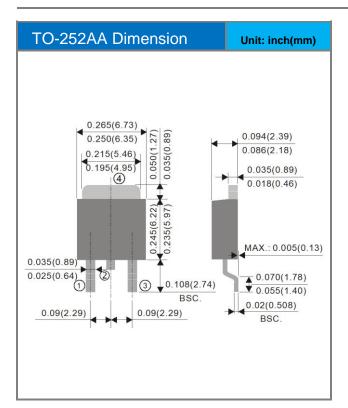


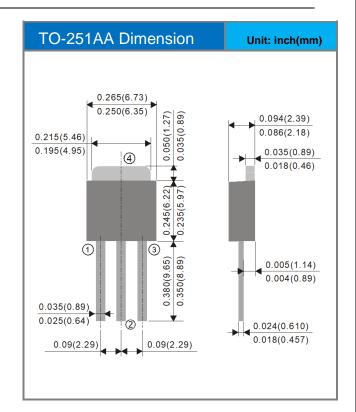
Fig.14 PJP35N06A Normalized Transient Thermal Impedance vs. Pulse Width

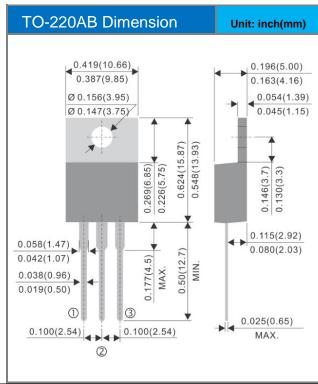




#### **Packaging Information**







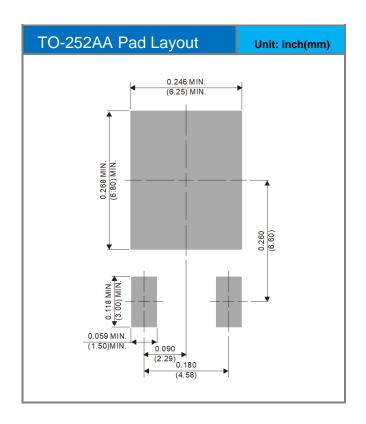




### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJU35N06A_T0_00001	TO-251AA	80pcs / Tube	U35N06A	Halogen free
PJD35N06A_L2_00001	TO-252AA	3,000pcs / 13" reel	D35N06A	Halogen free
PJP35N06A_T0_00001	TO-220AB	50pcs / Tube	P35N06A	Halogen free

### **Mounting Pad Layout**







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